Abstracts

Performance and Applications of Novel Tunable Oscillators Utilizing Focused-Ion-Beam-Implanted Gunn-Effect Devices

A. Chu, L. Chu, W. Macropoulos, K. Khair, R. Patel, M.H. Cordaro, L.J. Mahoney, H. Lezec and J. Melngailis. "Performance and Applications of Novel Tunable Oscillators Utilizing Focused-Ion-Beam-Implanted Gunn-Effect Devices." 1991 MTT-S International Microwave Symposium Digest 91.3 (1991 Vol. III [MWSYM]): 1179-1182.

The RF performance of novel tunable voltage-controlled, injection-locked and dielectric resonator oscillators utilizing focused-ion-beam-implanted (FIBI) Gunn-effect devices is reported for the first time. By varying the bias voltage across the device a frequency tuning range from 5 to 25 GHz was achieved, which is the widest band exhibited to date by a single FIBI Gunn oscillator.

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